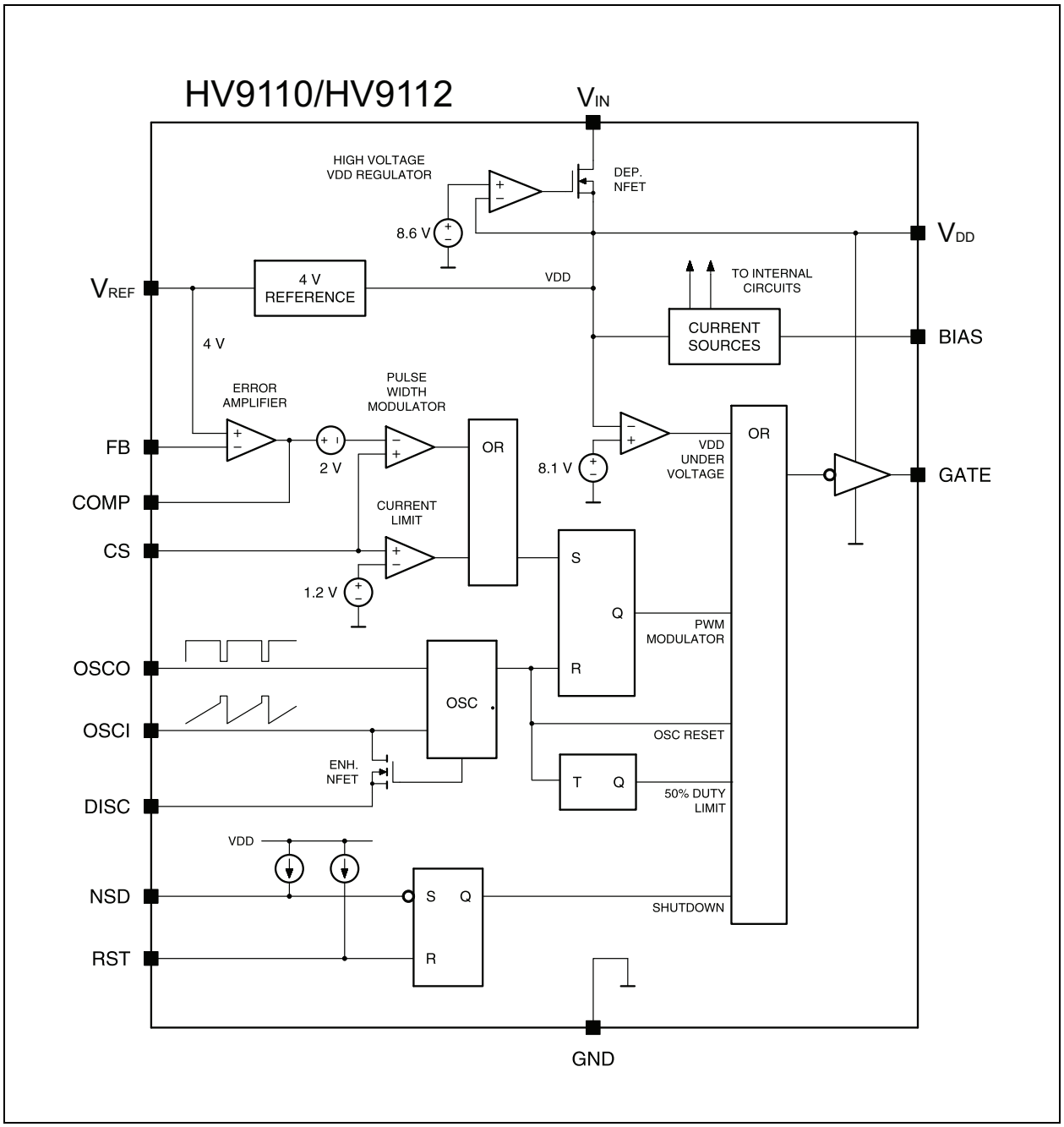
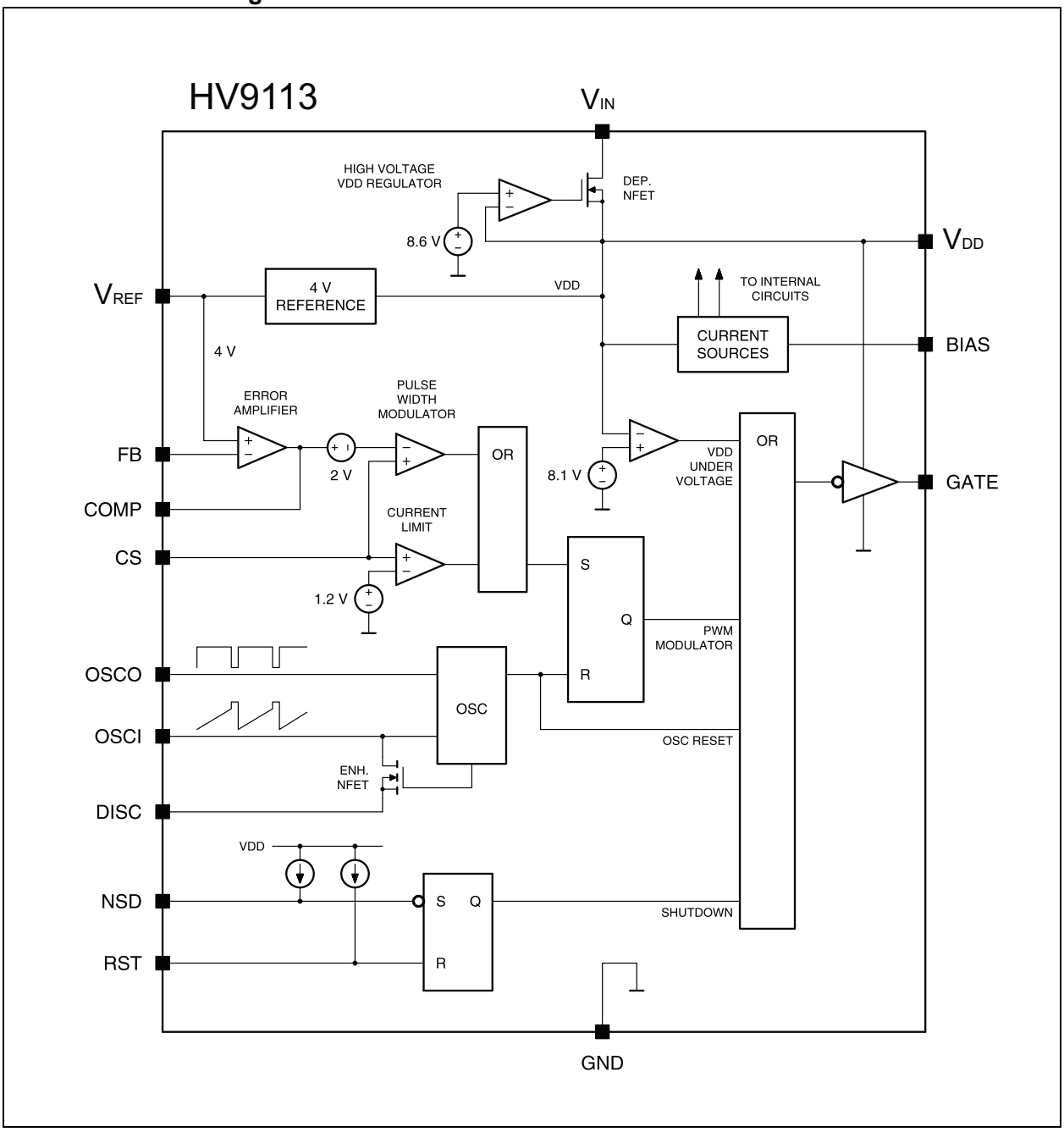
Functional Block Diagram



Functional Block Diagram



1.0 ELECTRICAL CHARACTERISTICS

ABSOLUTE MAXIMUM RATINGS†

Input Voltage, V_{IN}
- HV9110/HV9113 ..... 120V
- HV9112 ..... 80V

Device Supply Voltage, V_{DD} 15.5V
Logic Input Voltage Range ..... –0.3V to V_{DD} + 0.3V
Linear Input Voltage Range ..... –0.3V to V_{DD} + 0.3V
Storage Temperature Range ..... –65°C to +150°C
Operating Temperature Range ..... –55°C to +125°C
Power Dissipation: 14-lead SOIC ..... 750 mW

† Notice: Stresses above those listed under “Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

Electrical Specifications: V_{DD} = 10V, V_{IN} = 48V, V_{DISC} = 0V, R_{BIAS} = 390 kΩ, R_{OSC} = 330 kΩ, T_A= 25°C unless otherwise noted.

Parameters		Sym.	Min.	Typ.	Max.	Units	Conditions
REFERENCE							
Output Voltage	HV9110/13	V_{REF}	3.92	4	4.08	V	R_L = 10 MΩ
	HV9112		3.88	4	4.12		
	HV9110/13		3.82	4	4.16		R_L = 10 MΩ, T_A = –55°C to +125°C
Output Impedance		Z_{OUT}	15	30	45	kΩ	(**Note 1**)
Short Circuit Current		I_{SHORT}	—	125	250	µA	V_{REF} = GND
Change in V_{REF} with Temperature		ΔV_{REF}	—	0.25	—	mV/°C	T_A = –55°C to +125°C (**Note 1**)
OSCILLATOR							
Oscillator Frequency		f_{MAX}	1	3	—	MHz	R_{OSC} = 0Ω
Initial Accuracy		f_{OSC}	80	100	120	kHz	R_{OSC} = 330 kΩ (**Note**)
			160	200	240		R_{OSC} = 150 kΩ (**Note**)
V_{DD} Regulation		—	—	—	15	%	9.5V < V_{DD} < 13.5V
Temperature Coefficient		—	—	170	—	ppm/°C	T_A = –55°C to +125°C (**Note 1**)
PWM							
Maximum Duty Cycle	HV9110/HV9112	D_{MAX}	49	49.4	49.6	%	(**Note 1**)
	HV9113		95	97	99		
Dead Time	HV9113	D_{MIN}	—	225	—	ns	HV9113 only (**Note 1**)
Minimum Duty Cycle			—	—	0	%	
Pulse Width where Pulse drops out			—	80	125	ns	(**Note 1**)
CURRENT LIMIT							
Maximum Input Signal		V_{LIM}	1	1.2	1.4	V	V_{FB} = 0V
Delay to Output		t_D	—	80	120	ns	V_{CS} = 1.5V, V_{COMP} ≤ 2V (**Note 1**)

ELECTRICAL CHARACTERISTICS (CONTINUED)

Electrical Specifications: V_{DD} = 10V, V_{IN} = 48V, V_{DISC} = 0V, R_{BIAS} = 390 kΩ, R_{OSC} = 330 kΩ, T_A= 25°C unless otherwise noted.

Parameters		Sym.	Min.	Typ.	Max.	Units	Conditions
ERROR AMPLIFIER							
Feedback Voltage	HV9110/13	V_{FB}	3.96	4	4.04	V	V_{FB} shorted to COMP
	HV9112		3.92	4	4.08		
Input Bias Current		I_{IN}	—	25	500	nA	V_{FB} = 4V
Input Offset Voltage		V_{OS}	Nulled during trim			—	
Open-loop Voltage Gain		A_{VOL}	60	80	—	dB	(**Note 1**)
Unity Gain Bandwidth		GB	1	1.3	—	MHz	(**Note 1**)
Output Source Current		I_{SOURCE}	–1.4	–2	—	mA	V_{FB} = 3.4V
Output Sink Current		I_{SINK}	0.12	0.15	—	mA	V_{FB} = 4.5V
HIGH-VOLTAGE REGULATOR AND START-UP							
Input Voltage	HV9110/13	V_{IN}	—	—	120	V	I_{IN} < 10 µA; V_{CC} > 9.4V
	HV9112		—	—	80		
Input Leakage Current		I_{IN}	—	—	10	µA	V_{DD} > 9.4V
Regulator Turn-off Threshold Voltage		V_{TH}	8	8.7	9.4	V	I_{IN} = 10 µA
Undervoltage Lockout		V_{LOCK}	7	8.1	8.9	V	
SUPPLY							
Supply Current		I_{DD}	—	0.75	1	mA	C_L < 75 pF
Quiescent Supply Current		I_Q	—	0.55	—	mA	V_{NSD} = 0V
Nominal Bias Current		I_{BIAS}	—	20	—	µA	
Operating Range		V_{DD}	9	—	13.5	V	
SHUTDOWN LOGIC							
Shutdown Delay		t_{SD}	—	50	100	ns	C_L= 500 pF, V_{CS}= 0V (**Note 1**)
NSD Pulse Width		t_{SW}	50	—	—	ns	(**Note 1**)
RST Pulse Width		t_{RW}	50	—	—	ns	(**Note 1**)
Latching Pulse Width		t_{LW}	25	—	—	ns	V_{NSD}, V_{RST} = 0V(**Note 1**)
Input Low Voltage		V_{IL}	—	—	2	V	
Input High Voltage		V_{IH}	7	—	—	V	
Input Current, Input High Voltage		I_{IH}	—	1	5	µA	V_{IN} = V_{DD}
Input Current, Input Low Voltage		I_{IL}	—	–25	–35	µA	V_{IN} = 0V
OUTPUT							
Output High Voltage	HV9110/13	V_{OH}	V_{DD}–0.25	—	—	V	I_{OUT} = 10 mA
	HV9112		V_{DD}–0.3	—	—		
	HV9110/13		V_{DD}–0.3	—	—		I_{OUT} = 10 mA, T_A = –55°C to 125°C
Output Low Voltage	All	V_{OL}	—	—	0.2	V	I_{OUT} = –10 mA
	HV9110/13		—	—	0.3		I_{OUT} = –10 mA, T_A = –55°C to 125°C
Output Resistance	Pull up	R_{OUT}	—	15	25	Ω	I_{OUT} = ±10 mA
	Pull down		—	8	20		
	Pull up		—	20	30	Ω	I_{OUT} = ±10 mA, T_A = –55°C to 125°C
	Pull down		—	10	30		
Rise Time		t_R	—	30	75	ns	C_L = 500 pF (**Note 1**)
Fall Time		t_F	—	20	75	ns	C_L = 500 pF (**Note 1**)

Note 1: Design guidance only; Not 100% tested in production.
2: Stray capacitance on OSC input pin must be ≤5 pF.

TEMPERATURE SPECIFICATIONS

Parameters	Sym.	Min.	Typ.	Max.	Units	Conditions
TEMPERATURE RANGES						
Operating Temperature	—	–55	—	125	°C	
Storage Temperature	—	–65	—	150	°C	
PACKAGE THERMAL RESISTANCE						
14-lead SOIC	θ_{ja}	—	83	—	°C/W	

1.1 Truth Table

TRUTH TABLE

SHUTDOWN	RESET	OUTPUT
H	H	Normal operation
H	H → L	Normal operation, no change
L	H	Off, not latched
L	L	Off, latched
L → H	L	Off, latched, no change

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g. outside specified power supply range) and therefore outside the warranted range.

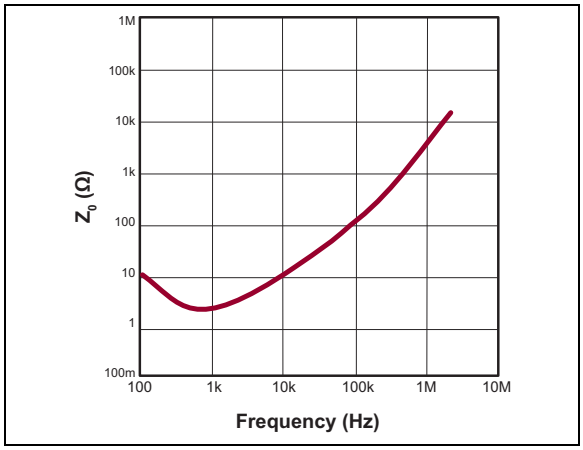


FIGURE 2-1: *Error Amplifier Output Impedance (Z_0).*

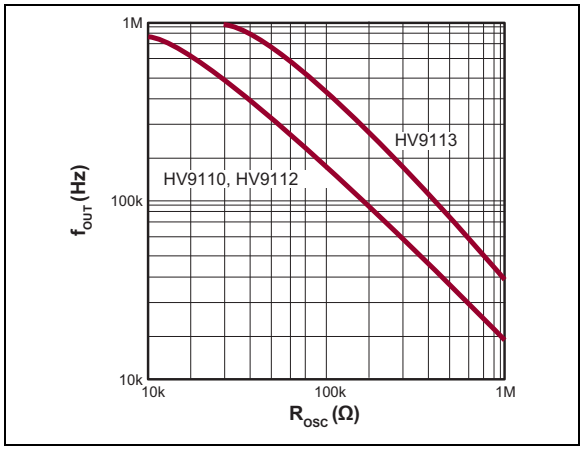


FIGURE 2-4: *Output Switching Frequency vs. Oscillator Resistance.*

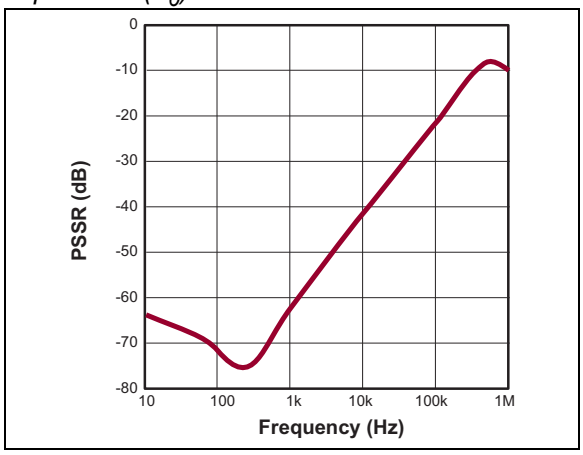


FIGURE 2-2: *PSRR –Error Amplifier and Reference.*

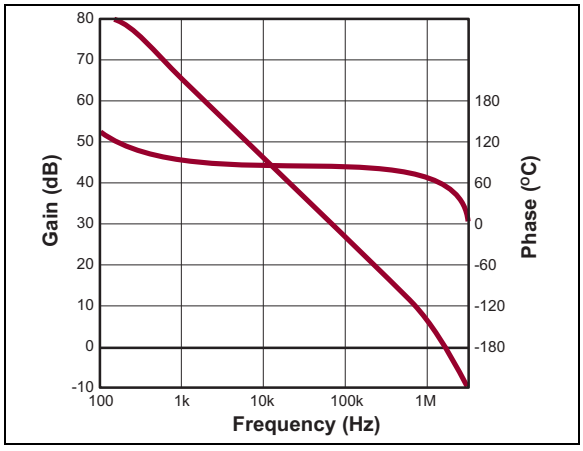


FIGURE 2-5: *Error Amplifier Open-loop Gain/Phase.*

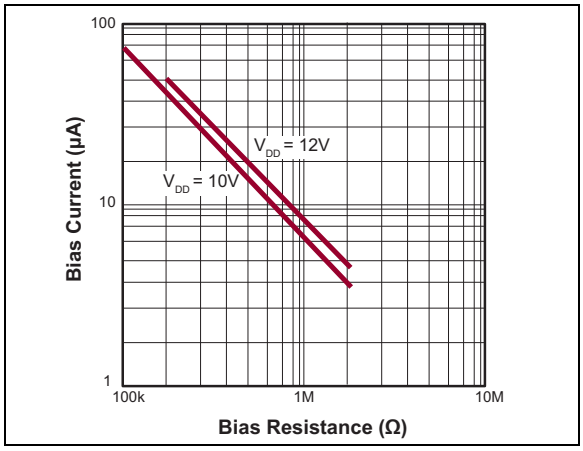


FIGURE 2-3: *Bias Current vs. Bias Resistance.*

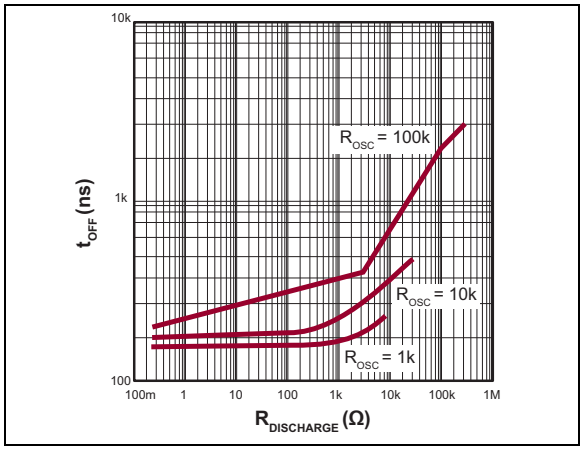


FIGURE 2-6: *$R_{DISCHARGE}$ vs. t_{OFF} (HV9113 only).*

3.0 PIN DESCRIPTION

Table 3-1 shows the pin description for HV9110/HV9112/HV9113. The locations of the pins are listed in Features.

TABLE 3-1: PIN DESCRIPTION

Pin Number	HV9110/HV9112/HV9113 Pin Name	Description
1	BIAS	Internal bias, current set
2	V_{IN}	High-voltage V_{DD} regulator input
3	CS	Current sense input
4	GATE	Gate drive output
5	GND	Ground
6	V_{DD}	High-voltage V_{DD} regulator output
7	OSCO	Oscillator output
8	OSCI	Oscillator input
9	DISC	Oscillator discharge, current set
10	V_{REF}	4V reference output Reference voltage level can be overridden by an externally applied voltage source.
11	NSD	Active low input to set shutdown latch
12	RST	Active high input to reset shutdown latch
13	COMP	Error amplifier output
14	FB	Feedback voltage input

4.0 TEST CIRCUITS

The test circuits for characterizing error amplifier output impedance, Z_{OUT}, and error amplifier, power supply rejection ratio, PSRR, are shown in Figure 4-1 and Figure 4-2.

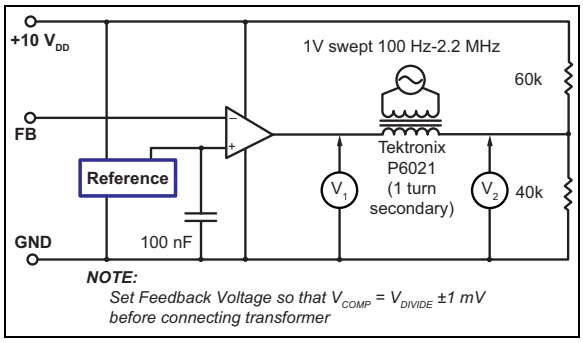


FIGURE 4-1: *Error Amp Z_{OUT}.*

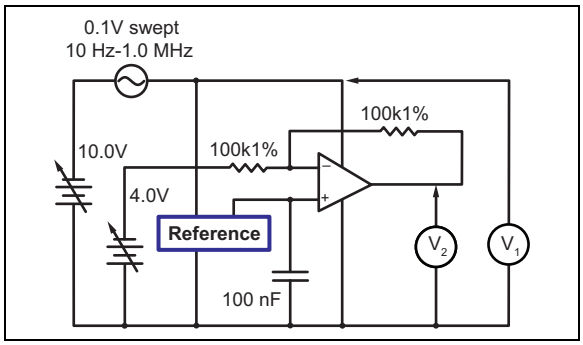


FIGURE 4-2: *PSRR.*

5.0 DETAILED DESCRIPTION

5.1 High-Voltage Regulator

The high-voltage regulator included in HV9110/HV9112/HV9113 consists of a high-voltage N-channel Depletion-mode DMOS transistor driven by an error amplifier, providing a current path between the V_{IN} terminal and the V_{DD} terminal. The maximum current, about 20 mA, occurs when V_{DD} = 0, with current reducing as V_{DD} rises. This path shuts off when V_{DD} rises to somewhere between 8V and 9.4V. So, if V_{DD} is held at 10V or 12V by an external source, no current other than leakage is drawn through the high voltage transistor. This minimizes dissipation within the high-voltage regulator.

Use an external capacitor between V_{DD} and GND. This capacitor should have good high-frequency characteristics. Ceramic caps work well.

The device uses a compound resistor divider to monitor V_{DD} for both the undervoltage lockout circuit and the shutoff circuit of the high-voltage FET. Setting the undervoltage sense point about 0.6V lower on the string than the FET shutoff point guarantees that the undervoltage lockout releases before the FET shuts off.

5.2 Bias Circuit

HV9110/HV9112/HV9113 require an external bias resistor, connected between the Bias pin and GND, to set currents in a series of current mirrors used by the analog sections of the chip. The nominal external bias current requirement is 15 µA to 20 µA, which can be set by a 390 kΩ to 510 kΩ resistor if V_{DD} = 10V, or a 510 kΩ to 680 kΩ resistor if V_{DD} = 12V. A precision resistor is not required, ±5% meets device requirements.

5.3 Clock Oscillator

The clock oscillator of the HV9110/HV9112/HV9113 consists of a ring of CMOS inverters, timing capacitors, and a capacitor-discharge FET. A single external resistor between the OSCI and OSCO sets the oscillator frequency. (See Figure 2-4.)

The HV9110 and HV9112 include a frequency-dividing flip-flop that allows the part to operate with a 50% duty limit. Accordingly, the effective switching frequency of the power converter is half the oscillator frequency. (See Figure 2-4.)

An internal discharge FET resets the oscillator ramp at the end of the oscillator cycle. The discharge FET is externally connected to GND, by way of a resistor. The resistor programs the oscillator dead time at the end of the oscillator period.

The oscillator turns off during shutdown to reduce supply current by about 150 µA.

5.4 Reference

The reference of the HV9110/HV9112/HV9113 consists of a band-gap reference, followed by a buffer amplifier, which scales the voltage up to 4V. The scaling resistors of the buffer amplifier are trimmed during manufacture so that the output of the error amplifier, when connected in a gain of –1 configuration, is as close to 4V as possible. This nulls out the input offset of the error amplifier. As a consequence, even though the observed reference voltage of a specific part may not be exactly 4V, the feedback voltage required for proper regulation will be 4V.

An approximately 50 kΩ resistor is located internally between the output of the reference buffer amplifier and the circuitry it feeds—reference output pin and non-inverting input to the error amplifier. This allows overriding the internal reference with a low impedance voltage source ≤ 6V. Using an external reference reinstates the input offset voltage of the error amplifier. Overriding the reference should seldom be necessary.

The reference of the HV9110/HV9112/HV9113 is a high-impedance node, and usually there will be significant electrical noise nearby. Therefore, a bypass capacitor between the reference pin and GND is strongly recommended. The reference buffer amplifier is compensated to be stable with a capacitive load of 0.01 µF to 0.1 µF.

5.5 Error Amplifier

The error amplifier on HV9110/HV9112/HV9113 is a low-power, differential-input, operational amplifier. A PMOS input stage is used, so the common mode range includes ground and the input impedance is high.

5.6 Current Sense Comparators

The HV9110/HV9112/HV9113 use a dual-comparator system with independent comparators for modulation and current limiting. This provides the designer greater latitude in compensation design, as there are no clamps, except ESD protection, on the compensation pin.

5.7 Remote Shutdown

The NSD and RST pins control the shutdown latch. These pins have internal current-source pull-ups so they can be driven from open drain logic. When not used they should be left open or connected to V_{DD}.

5.8 Output Buffer

The output buffer of HV9110/HV9112/HV9113 is of standard CMOS construction P-channel pull-up and N-channel pull-down. Thus, the body-drain diodes of the output stage can be used for spike clipping. External Schottky diode clamping of the output is not required.

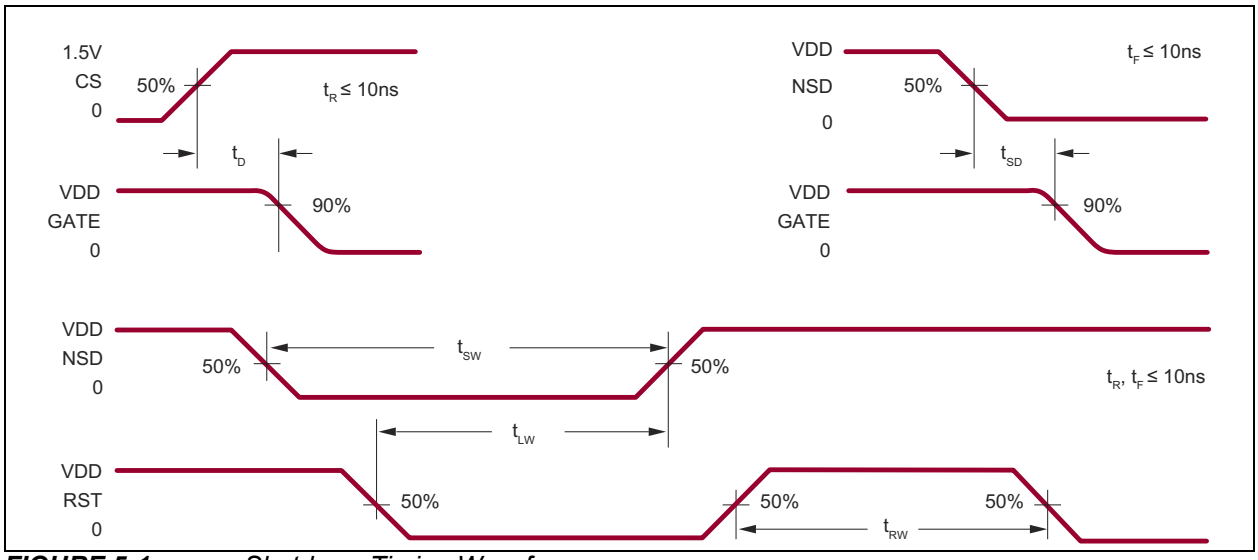
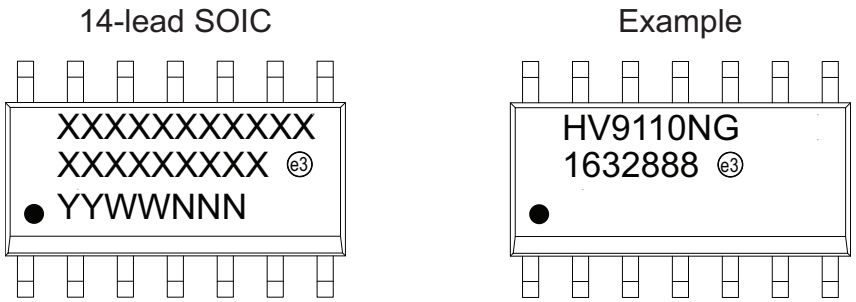


FIGURE 5-1: *Shutdown Timing Waveforms.*

6.0 PACKAGING INFORMATION

6.1 Package Marking Information

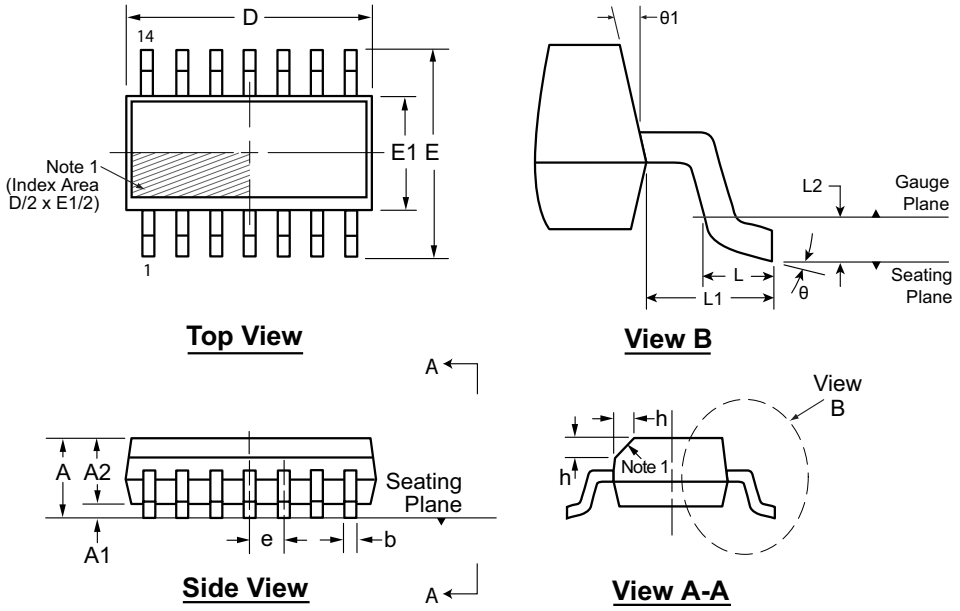


Legend:	XX...X	Product Code or Customer-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week ‘01’)
	NNN	Alphanumeric traceability code
	(e3)	Pb-free JEDEC® designator for Matte Tin (Sn)
	*	This package is Pb-free. The Pb-free JEDEC designator ((e3)) can be found on the outer packaging for this package.

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for product code or customer-specific information. Package may or not include the corporate logo.

14-Lead SOIC (Narrow Body) Package Outline (NG)

8.65x3.90mm body, 1.75mm height (max), 1.27mm pitch



Note: For the most current package drawings, see the Microchip Packaging Specification at www.microchip.com/packaging.

Note:

1. *This chamfer feature is optional. If it is not present, then a Pin 1 identifier must be located in the index area indicated. The Pin 1 identifier can be: a molded mark/identifier; an embedded metal marker; or a printed indicator.*

Symbol		A	A1	A2	b	D	E	E1	e	h	L	L1	L2	θ	θ1
Dimension (mm)	MIN	1.35*	0.10	1.25	0.31	8.55*	5.80*	3.80*	1.27 BSC	0.25	0.40	1.04 REF	0.25 BSC	0°	5°
	NOM	-	-	-	-	8.65	6.00	3.90		-	-			-	-
	MAX	1.75	0.25	1.65*	0.51	8.75*	6.20*	4.00*		0.50	1.27			8°	15°

JEDEC Registration MS-012, Variation AB, Issue E, Sept. 2005.
** This dimension is not specified in the JEDEC drawing.*
Drawings are not to scale.

NOTES:

APPENDIX A: REVISION HISTORY

Revision A (June 2016)

- Merged Supertex Doc #s DSFP-HV9110, DSFP-HV9112 and DSFP-DSFP-HV9113 to Microchip DS20005505A.
- Revised **Electrical Characteristics** to accommodate the merged products.
- Updated pin names to reflect new naming convention.
- Significant text changes to **Detailed Description**.
- Minor text changes throughout.

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO.	XX	-	X	-	X
Device	Package Options		Environmental		Media Type

Device:	HV9110 =	High-voltage Current-mode PWM Controller, 10V to 120V Input Voltage Range, 49% Duty Cycle
	HV9112 =	High-voltage Current-mode PWM Controller, 9V to 80V Input Voltage Range, 49% Duty Cycle
	HV9113 =	High-voltage Current-mode PWM Controller, 10V to 120V Input Voltage Range, 99% Duty Cycle
Package:	NG =	14-lead SOIC
Environmental	G =	Lead (Pb)-free/RoHS-compliant Package
Media Type:	(blank) =	53/Tube for an NG package

Examples:

a) HV9110NG-G: High-voltage Current-mode PWM Controller 10V to 120V Input Voltage Range, 49% Duty Cycle, 14-lead SOIC Package, 53/Tube

b) HV9112NG-G: High-voltage Current-mode PWM Controller, 9V to 80V Input Voltage Range, 49% Duty Cycle,14-lead SOIC Package, 53/Tube

c) HV9113NG-G: High-voltage Current-mode PWM Controller, 10V to 120V Input Voltage Range, 99% Duty Cycle, 14-lead SOIC Package, 53/Tube

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